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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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1

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Complete if Known

Application Number	10/638,406
Filing Date	August 12, 2003
First Named Inventor	Koji Sakui et al.
Group Art Unit	2818
Examiner Name	Unknown
Attorney Docket Number	01701.00236

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number ⁴	Kind Code ⁵ (if known)			
ap		5515327		Matsukawa et al.	5-7-1996	
		5559735		Ono et al.	9-24-1996	
		5523980		Sakui et al.	6-4-1996	
		5615163		Sakui et al.	3-25-1997	
ap		4996669		Endoh et al.	2-26-1991	

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
ap		EP	0797212	A2	Toshiba	9-24-1997		x
ap		JP	10-177797	A	Toshiba	6-30-1998		abst

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
ap		Takeuchi, Ken, et al., "A Double-Level-V _{th} Select Gate Array Architecture for Multilevel NAND Flash Memories," IEICE Trans. Electron., Vol. E79-C, No. 7, July 1, 1996, pp. 1013-1020	
ap		Choi, J.D., et al., "A New Double Boosting Program Scheme in Booster Plate NAND Flash Memories with 9V Programming," Non-Volatile Semiconductor Memory Workshop, August 1998, pp. 109-111	

Examiner Signature

Date Considered

6/2/04

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				Filing Date		Herewith
				First Named Inventor		Koji Sakui et al.
				Group Art Unit	Unknown	
				Examiner Name	Unknown.	
Sheet	1	of	2	Attorney Docket Number	01701.00236	

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Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₈
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
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Sheet	2	of	2
		Examiner Name	Koji Sakui et al.
		Group Art Unit	Unknown
		Attorney Docket Number	01701.00236

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ap		"SESSION XII: ROMs, PROMs AND EROMs TPHM 12.6:A 16Kb Electrically Erasable Nonvolatile Memory", William S. Johnson, et al. ISSCC 80/1980, IEEE International Solid-State Circuits Conference, CH 1490-2/80/0000/0152, pp. 152-153, Feb. 14, 1980	
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ap		European Search Report dated September 22, 2000	
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ap		Atsushi Nozoe et al., ISSCC99/Session 6/Paper MP6.5, "A 256 Mb Multilevel Flash Memory with 2MB/s Program Rate for Mass Storage Applications," pp. 1-6	

Examiner Signature	<i>Ash Phung</i>	Date Considered	6/2/04
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